What is claimed is:

1. A display device structure with compensating electrodes, wherein the display device is composed of a first substrate, a second substrate and a liquid crystal layer formed therebetween, a pixel composed of a plurality of compensating electrodes is formed on the first substrate, the pixel is comprised of a plurality of first and second electrodes, a insulating layer is disposed between the first and the second electrodes, and each pixel comprising:

a first sub-pixel, wherein the first sub-pixel is divided into a first domain and a second domain;

a second sub-pixel, wherein the second sub-pixel is adjacent to the first sub-pixel and divided into a third domain and a fourth domain; and

a third sub-pixel, wherein the third sub-pixel is adjacent to the second sub-pixel and divided into a fifth domain and a sixth domain;

wherein the first electrodes and the second electrodes are parallel to each other in each pixel, the first electrodes are below the second electrodes in the first, fourth and fifth domains, and the first electrodes are over the second electrodes in the second, third, and sixth domain.

2. The structure as claimed in claim 1, wherein the third domain is adjacent to the first, fourth, and fifth domains, and the third domain is diagonal to the second and the sixth domains.

3. The structure as claimed in claim 1, wherein the fourth domain is adjacent to the second, third, and sixth domains, and the fourth domain is diagonal to the first and the fifth domains.

4. The structure as claimed in claim 1, wherein the first electrodes are first comb type electrodes, and the second electrodes are second comb type electrodes.

5. The structure as claimed in claim 1, wherein the first electrodes are formed of non-transparent materials, and the non-transparent materials are Al or MoW.

6. The structure as claimed in claim 1, wherein the second electrodes are formed of transparent materials, and the transparent materials are ITO or IZO.

7. A display device structure with compensating electrodes, comprising:

a first substrate, wherein the first substrate includes a first, second, third, and fourth domains, arranged in a matrix, the first domain and the second domain are parallel in the same column, the third and the fourth domains are in the same column, the first and the third

domains are in the same row, the second and the fourth domains are in the same row;

a gate line, wherein the gate line extends along a first direction on the first substrate;

a first data line, wherein the first data line extends along a second direction on the first substrate;

a plurality of TFTs, wherein the TFTs are disposed on the matrix and connected to the first data line and the gate line;

a plurality of first electrodes, wherein the first electrodes are respectively formed in the first, second, third and fourth domains, and

a plurality of second electrodes, wherein the second electrodes are respectively formed in the first, second, third and fourth domains;

wherein the second electrodes are electrically connected to the TFTs;

wherein the first electrodes in the second and third domains are respectively electrically connected to the first electrodes in the fourth and first domains,

wherein the positions of the first and second electrodes are the same in the diagonal domains, and the positions of the first and second electrodes are reversed in the adjacent domains.

8. The structure as claimed in claim 7, wherein the first direction is perpendicular to the second direction.

9. The structure as claimed in claim 7, wherein the TFTs include a first TFT and a second TFT.

10. The structure as claimed in claim 9, wherein the first TFT is on the left side of the intersection of the gate line and the first data line connecting the second electrodes in the first and the second domains, and the second TFT is on the right side of the intersection of the gate line and the first data line connecting the second electrodes in the third and the fourth domains.

11. The structure as claimed in claim 9, further comprising a second data line extending along the second direction on the first substrate.

12. The structure as claimed in claim 11, wherein the first TFT is on the left side of the intersection of the gate line and the first data line connecting the second electrodes in the first and the second domains, and the second TFT is on the left side of the intersection of the gate line and the second data line connecting the second electrodes in the third and the fourth domains.

13. The structure as claimed in claim 11, wherein the first TFT is on the right side of the intersection of the gate line and the first data line connecting the

second electrodes in the first and the second domains, and the second TFT is on the right side of the intersect point of the gate line and the second data line connecting the second electrodes in the third and the fourth domains.

14. The structure as claimed in claim 9, wherein the first electrodes in the first domain include a first common line extending along the first direction, the first electrodes in the fourth domain include a second common line extending along the first direction, the first electrodes in the first domain are connected to the first electrodes in the third domain through the first common line, and the first electrodes in the fourth domain are connected to the first electrodes in the second domain through the second common line.

15. The structure as claimed in claim 14, wherein the second electrodes in the second domain are connected to the first TFT through a first contact hole, and the second electrodes in the third domain are connected to the second TFT through a second contact hole.

16. The structure as claimed in claim 14, wherein the first electrodes in the third domain are connected to the first common line through a third contact hole, and the first electrodes in the second domain are connected to the second common line through a fourth contact hole.

17. The structure as claimed in claim 7, wherein the first electrodes are first comb type electrodes, and the second electrodes are second comb type electrodes.

18. The structure as claimed in claim 17, wherein

the first comb type electrodes in the first and fourth domains include a plurality of branches extending along a third direction;

the first comb type electrodes in the second and third domains include a plurality of branches extending along a fourth direction;

the second comp type electrodes in the first domain include a first comb stem near the gate line and a plurality of branches extending along the third direction from the first comb stem;

the second comp type electrodes in the second domain include a second comb stem near the gate line and a plurality of branches extending along the fourth direction from the second comb stem;

the second comp type electrodes in the third domain include a third comb stem near the gate line and a plurality of branches extending along the fourth direction from the third comb stem;

the second comp type electrodes in the fourth domain include a fourth comb stem near the gate line and a plurality of branches extending along the third direction from the fourth comb stem; and

the first comb type electrodes and the second comb type electrodes are intersecting with each other.

19. The structure as claimed in claim 17, wherein the third direction is the direction of clock-wise rotation from the second direction at an angle between 5° to 15°.

20. The structure as claimed in claim 17, wherein the fourth direction is the direction of counter clock-wise rotation from the second direction at an angle between 5° to 15°.